RB751V-40 SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

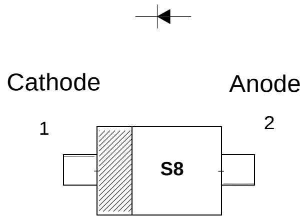
Features

- Small surface mounting type
- Low reverse current and low forward voltage
- High reliability

Applications

- High speed switching

Marking Code: "**S8**"



SOD-323

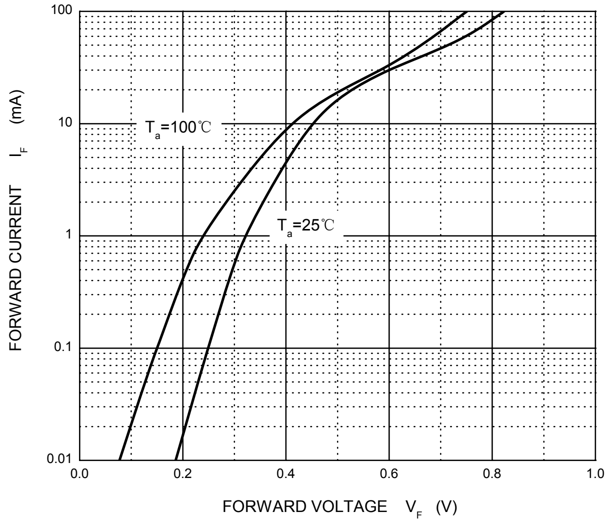
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	Limit	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_O	0.03	A
Non-repetitive Peak Forward Surge Current@t=8.3ms	I_{FSM}	0.2	A
Power dissipation	P_D	200	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	500	℃/W
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55~+150	℃

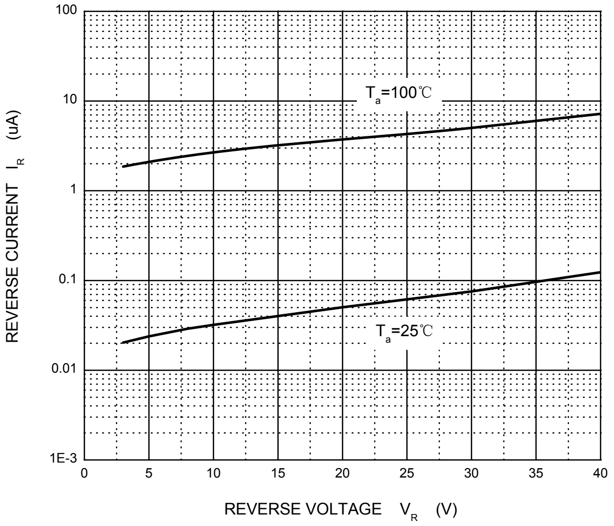
Characteristics at T_a = 25 °C

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at I_F = 1 mA	V_F	-	0.37	V
Reverse Current at V_R = 30 V	I_R	-	0.5	µA
Capacitance Between Terminals at V_R = 1 V, f = 1 MHz	C_T	2	-	pF

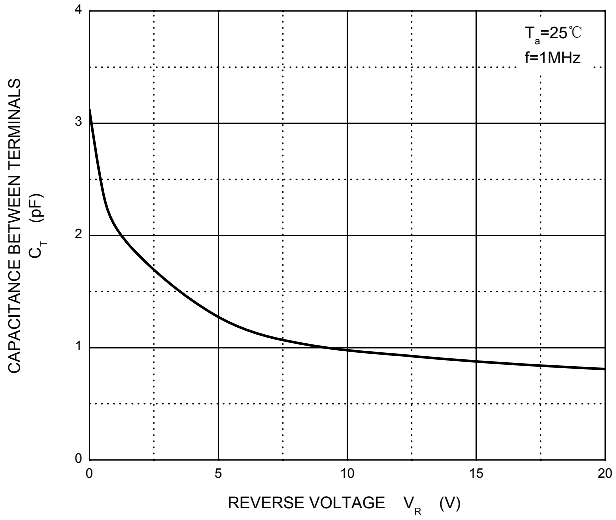
Note: ESD sensitive product handling required.



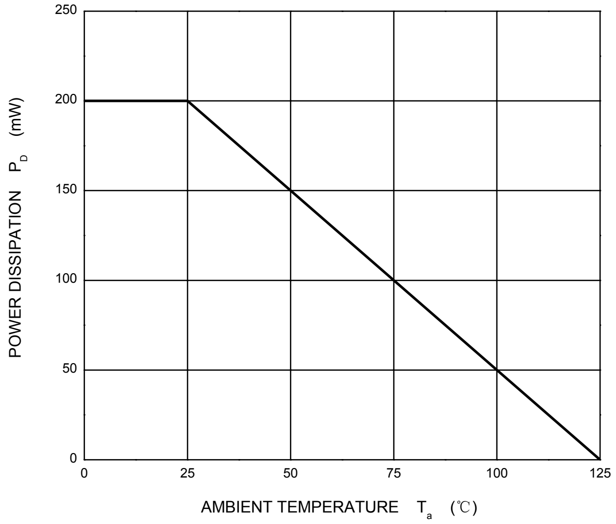
Forward Characteristics



Reverse Characteristics



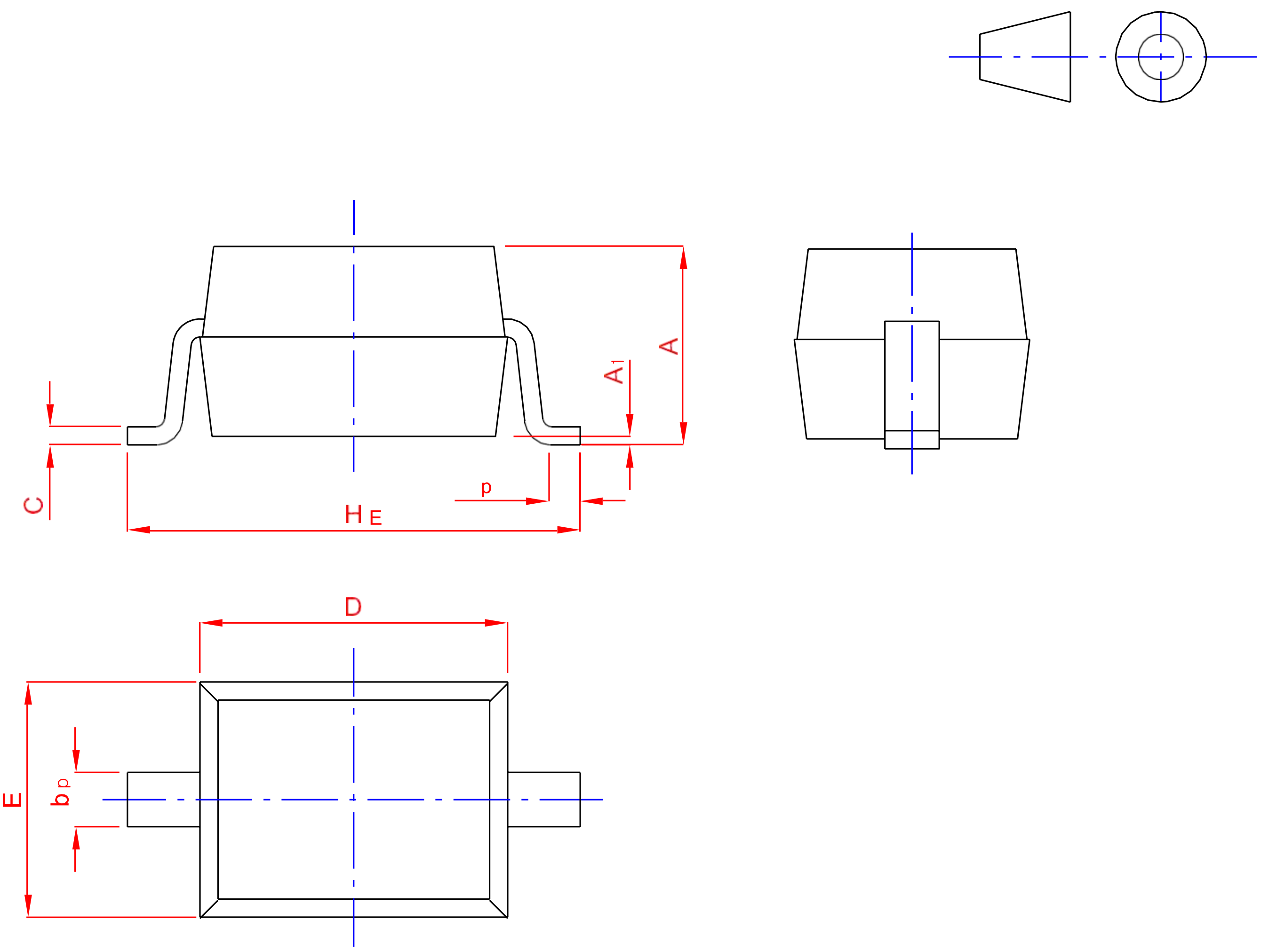
Capacitance Characteristics



Power Derating Curve

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads



UNIT	A	b_p	C	D	E	H_E	A_1	L_p
mm	1.00 0.80	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20